

IN THE CLAIMS

Please amend the claims as follows:

1 (Currently Amended): A power semiconductor device, comprising:

plural power semiconductor elements which have a control electrode and a first and a second current electrodes, respectively, and said first current electrodes are connected with each other and said second current electrodes are connected with each other, respectively; and a control part controlling said plural power semiconductor elements, wherein said control part repeats a regional control operation to operate a first group of said plural power semiconductor elements by providing a first input signal for each of said control electrodes of said first group, ~~and to operate a first group of said plural semiconductor elements by providing a first input signal for each of said control electrodes of said first group,~~ and to operate a second group of said plural power semiconductor elements by providing a second input signal for each of said control electrodes of the second group after an operation of said first group is finished.

2 (Previously Presented): The power semiconductor device according to claim 1, wherein

said control part can select either performing a general control operation activating all of said plural power semiconductor elements identically by providing said first and second input signals for all of said control electrodes of the first and second groups or repeating said regional control operation.

3 (Previously Presented): The power semiconductor device according to claim 1, wherein said first and second input signals consist of a pulse row, and

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plural power semiconductor elements which have a control electrode and a first and a second current electrodes, respectively, and said first current electrodes are connected with each other and said second current electrodes are connected with each other, respectively; and
a control part controlling said plural power semiconductor elements, wherein
said control part repeats a regional control operation to operate a first group of said plural power semiconductor elements by providing a first input signal for each of said control electrodes of said first group, ~~and to operate a first group of said plural semiconductor elements by providing a first input signal for each of said control electrodes of said first group,~~ and to operate a second group of said plural power semiconductor elements by providing a second input signal for each of said control electrodes of the second group after an operation of said first group is finished.

2 (Previously Presented): The power semiconductor device according to claim 1, wherein

said control part can select either performing a general control operation activating all of said plural power semiconductor elements identically by providing said first and second input signals for all of said control electrodes of the first and second groups or repeating said regional control operation.

3 (Previously Presented): The power semiconductor device according to claim 1, wherein said first and second input signals consist of a pulse row, and

said control part performs said operation of said first group and an operation of said second group in said regional control operation on each pulse basis.

4 (Previously Presented): The power semiconductor device according to claim 1, further comprising:

at least one detecting part detecting information corresponding to an operating condition of said plural power semiconductor elements, wherein

said detecting part provides said information for said control part and

said control part selects said first group and said second group of said plural power semiconductor elements being made to operate when said regional control operation is performed on the basis of said information.

5 (Previously Presented): The power semiconductor device according to claim 4, wherein

said at least one detecting part comprises plural detecting parts, and

said plural detecting parts are employed corresponding to said plural power semiconductor elements, respectively.

6 (Currently Amended): The power semiconductor device according to claim 4, wherein

said detecting part is ~~unit~~ comprises a temperature sensor, and said information is an operating temperature of ~~one of~~ said power semiconductor elements.

7 (Currently Amended): The power semiconductor device according to claim 4, wherein

said detecting part is unit ~~comprises~~ a current detector, and said information is a current flowing between said first and said second current electrodes of ~~one of~~ said power semiconductor elements.

8 (Currently Amended): The power semiconductor device according to claim 4, wherein

said detecting part is unit ~~comprises~~ a voltage detector, and said information is a voltage between said first and said second current electrodes of ~~one of~~ said power semiconductor element.

9 (Previously Presented): The power semiconductor device according to claim 8, wherein

said control part also operates at least one of said second group of said plural power semiconductor elements in addition to said first group, in case a backward voltage between said first and said second current electrodes of said first group of said plural power semiconductor elements exceeds a predetermined value, when said regional control operation is performed.